NSN 5961-01-202-8242

No Fiig: A110a0

Unitized Semiconductor Devices - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-202-8242 **Inclosure Material:** Ceramic or metal **Overall Length:** 0.310 inches **Overall Height:** 0.080 inches **Overall Width:** 0.380 inches Joint Electronic Device Engineering Council/jedec/case Outline Designation: T0-86 **Component Name And Quantity:** 4 transistor **Mounting Method: Terminal Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon all transistor Voltage Rating In Volts Per Characteristic: 50.0 collector to base voltage, dc all transistor and 50.0 collector to emitter voltage, dc all transistor and 6.0 emitter to base voltage, dc all transistor **Current Rating Per Characteristic:** 1.00 amperes source cutoff current all transistor **Power Rating Per Characteristic:** 500.0 milliwatts small-signal input power, common-collector absolute all transistor **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius ambient air **Special Features:** All transistor junction pattern arrangement: npn **Test Data Document:** 17981-012044 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing) **Terminal Type And Quantity:** 14 printed circuit Shelf Life: N/a **Unit Of Measure: Demilitarization:**